

isc N-Channel MOSFET Transistor

2SK959

DESCRIPTION

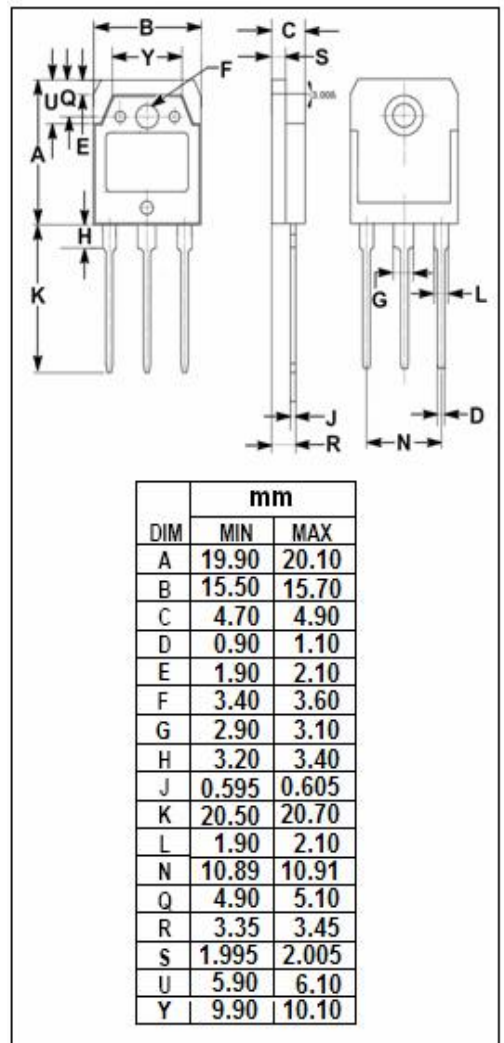
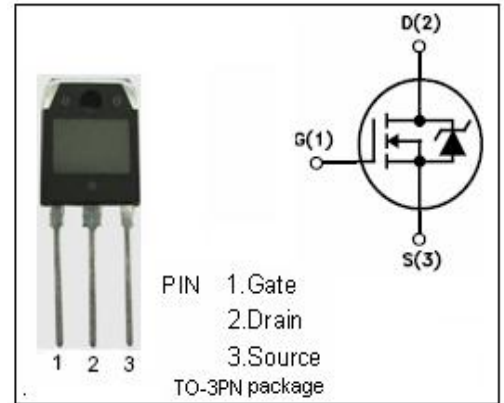
- Drain Current $-I_D=2A @ T_C=25^\circ C$
- Drain Source Voltage-
: $V_{DSS}=900V(\text{Min})$

APPLICATIONS

- Designed especially for high voltage.
- high speed applications.

ABSOLUTE MAXIMUM RATINGS($T_a=25^\circ C$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{DSS}	Drain-Source Voltage ($V_{GS}=0$)	900	V
V_{GS}	Gate-Source Voltage	± 20	V
I_D	Drain Current-continuous@ $T_C=25^\circ C$	2	A
P_{tot}	Total Dissipation@ $T_C=25^\circ C$	80	W
T_j	Max. Operating Junction Temperature	80	$^\circ C$
T_{stg}	Storage Temperature Range	-55~150	$^\circ C$



isc N-Channel MOSFET Transistor**2SK959****• ELECTRICAL CHARACTERISTICS (T_c=25°C)**

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
(BR)DSS	Drain-Source Breakdown Voltage	V _{GS} =0; I _D = 1mA	900			V
V _{GS(TH)}	Gate Threshold Voltage	V _{DS} = V _{GS} ; I _D = 1mA	2.5	3.5	5.0	V
R _{DS(ON)}	Drain-Source On-stage Resistance	V _{GS} = 10V; I _D =1A			8.5	Ω
I _{GSS}	Gate Source Leakage Current	V _{GS} = ±20V; V _{DS} = 0			±100	nA
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =900V; V _{GS} = 0			500	uA